

**High Current and Performance White LED Driver**

**Features**

- Efficiency up to 85% at  $V_{IN}=3.6V$ , 9LEDs,  $I_{LED}=20mA$
- 1.2MHz fixed switching frequency
- Low Standby Current:  $0.1\mu A$ ,  $V_{EN}=0V$  (typ.)
- Matches LED current
- Tiny inductor and capacitors
- Up to 9 strings White-LED
- Tiny 6-lead SOT23-6 package
- Built in OVP, OCP, OTP, UVLO protection

**Applications**

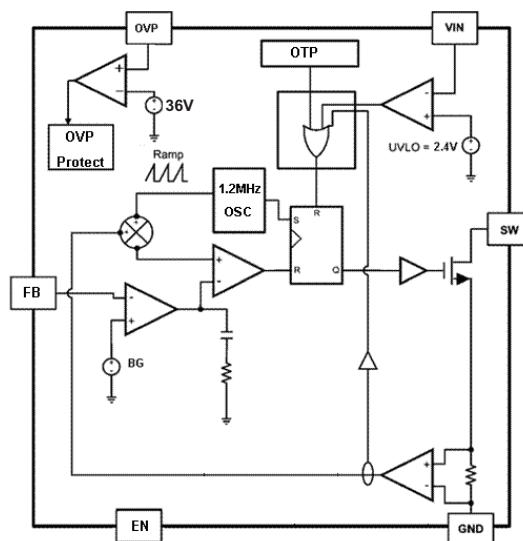
- Cellular phones
- PDAs
- DSCs
- GPS
- Handheld devices
- White LED display backlighting

**General Description**

HT7938 is high efficiency boost converter with constant current output to provide backlight in handheld devices. Series connection of LEDs provides constant identical LED currents resulting in uniform brightness. The continuous LED current is set with FB pin regulated voltage across an external sense resistor ( $R_{FB}$ ) connected from

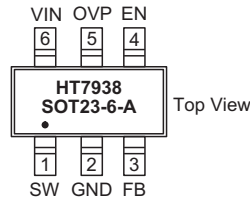
that pin to ground. The built-in open load protection prevents the damage resulting from an open circuit condition. Low 200mV feedback voltage minimizes power loss in the current setting resistor for better efficiency. HT7938 switches at rates up to 1.2MHz to allow the use of extremely small inductor and filter capacitor.

**Block Diagram**



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**Pin Assignment**



**Pin Description**

Pin Name	I/O	Description
EN	I	Shutdown & Dimming control input. Don't allow this pin to float.
GND	—	Signal Ground.
FB	I	Feedback pin. Reference voltage. The HT7938 feedback voltage is 200mV. Connect the sense resistor from FB to GND to set the LED current. Calculate resistor value according to $R_{FB} = \frac{200mV}{I_{LED}}$ .
SW	I	Switching pin. Internal power MOSFET drain. Connected to inductor and diode.
VIN	I	Input supply pin. The input supply pin for the IC. Connect VIN to a supply voltage between 2.6V~5.5V.
OVP	O	Over voltage protection pin which is connected to the output.

**Absolute Maximum Ratings**

Input Voltage.....	6.0V	SW Voltage.....	46V
FB Voltage.....	6.0V	EN .....	6.0V
OVP Voltage .....	46V	Operating Temperature Range .....	-40°C to +85°C
Storage Temperature Range .....	-55°C to +150°C	Maximum Junction Temperature.....	+150°C

Note: These are stress ratings only. Stresses exceeding the range specified under "Absolute Maximum Ratings" may cause substantial damage to the device. Functional operation of this device at other conditions beyond those listed [www.DataSheet4U.com](http://www.DataSheet4U.com) in the specification is not implied and prolonged exposure to extreme conditions may affect device reliability.

**Electrical Characteristics**
 $V_{IN}=3.6V, L=10\mu H, C_{IN}=1\mu F, C_O=1\mu F, I_{LED}=20mA, T_a=25^\circ C$ 

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{IN}$	Input Voltage	—	2.6	—	5.5	V
ULVO	Under Voltage Lockout	—	—	2.4	2.5	V
$I_{IN}$	Supply Current	Switching, $V_{FB}=GND$	—	1.0	2.5	mA
		$V_{EN}=0V$	—	0.1	1.0	$\mu A$
		$V_{FB}=0.2V$ , not switching	—	200	300	$\mu A$
<b>Error Amplifier</b>						
$V_{FB}$	Feedback Voltage	—	190	200	210	mV
<b>Power Switch</b>						
$f_{OSC}$	Switching Frequency	Measurement at SW pin	0.8	1.2	1.6	MHz
DC	Maximum Duty Cycle		92	95	—	%
$R_{DS(ON)}$	SW On Resistance	—	—	0.9	—	$\Omega$
$I_{SW(OFF)}$	Switch Leakage Current	—	—	0.1	1.0	$\mu A$
<b>EN Pin</b>						
$V_{IH}$	EN Voltage High	$V_{IN}=2.6V\sim 5.5V$	2.0	—	—	V
$V_{IL}$	EN Voltage Low	$V_{IN}=2.6V\sim 5.5V$	—	—	0.8	V
<b>OVP and OCP</b>						
$V_{OVP}$	OVP Threshold	No load	33	36	39	V
$I_{OCP}$	N-channel MOSFET Current Limit	—	—	750	—	mA
<b>Thermal Shutdown</b>						
$T_{SHUT}$	Thermal Shutdown Threshold	—	—	150	—	$^\circ C$
	Thermal Shutdown Hysteresis	—	—	15	—	$^\circ C$

## Function Description

### VIN Under-Voltage Lockout – UVLO

The device contains an Input Under Voltage Lockout (UVLO) circuit. The purpose of the UVLO circuit is to ensure that the input voltage is high enough for reliable operation. When the input voltage falls below the under voltage threshold, the internal FET switch is turned off. If the input voltage rises by the under voltage lockout hysteresis, the device will restart. The UVLO threshold is set below the minimum input voltage of 2.6V to avoid any transient VIN drops under the UVLO threshold and causing the converter to turn off.

### Current Limit Protection

The device has a cycle-by-cycle current limit to protect the internal power MOSFET. If the inductor current reaches the current limit threshold, the MOSFET will be turned off. It is important to note that this current limit will not protect the output from excessive current during an output short circuit. If an output short circuit has occurred, excessive current can damage both the inductor and diode.

### Over-Voltage Protection – OVP

The device provides an over-voltage protection function. If the FB pin is shorted to ground or an LED is disconnected from the circuit, the FB pin voltage will fall to zero and the internal power MOSFET will switch with its full duty cycle. This may cause the output voltage to exceed its maximum voltage rating, possibly damaging the IC and external components. Internal over-voltage protection circuitry turns off the power MOSFET and shuts down the IC as soon as the output voltage exceeds the  $V_{OVP}$  threshold. As a result, the output voltage falls to the level of the input supply voltage. The device remains in shutdown mode until the power is recycled.

### Over-Temperature protection – OTP

A thermal shutdown is implemented to prevent damages due to excessive heat and power dissipation. Typically the thermal shutdown threshold is 150°C. When the thermal shutdown is triggered the device stops switching until the temperature falls below typically 135°C. Then the device starts switching again.

### Application Information

- Inductor Selection

The selection of the inductor affects steady state operation as well as transient behavior and loop stability. There are three important electrical parameters which need to be considered when choosing an inductor: the value of inductor, DCR (copper wire resistance) and the saturation current.

Choose an inductor that can handle the necessary peak current without saturating, and ensure that the inductor has a low DCR to minimise power losses. A 10μH~22μH inductor should be a good choice for most HT7938 applications. However, a more exact inductance value can be calculated. A good rule for choosing an inductor value is to allow the peak-to-peak ripple current to be approximately 30~50% of the maximum input current. Calculate the required inductance value using the following equation:

$$L = \frac{V_{IN} \times (V_{OUT} - V_{IN})}{V_{OUT} \times F_{SW} \times \Delta I_L}$$

$$I_{IN(MAX)} = \frac{V_{OUT} \times I_{OUT(MAX)}}{V_{IN} \times \eta}$$

$$\Delta I_L = (30\% \sim 50\%) \times I_{IN(MAX)}$$

$$I_{L(PEAK)} = I_{IN(MAX)} + \frac{1}{2} \Delta I_L$$

In the equation above,  $I_{OUT(MAX)}$  is the maximum load current,  $\Delta I_L$  is the peak-to-peak inductor ripple current,  $\eta$  is the converter efficiency,  $F_{SW}$  is the switching frequency and  $I_{L(PEAK)}$  is the peak inductor current.

- Output Capacitor Selection

The output capacitor determines the steady state output voltage ripple. The voltage ripple is related to the capacitor's capacitance and its ESR (Equivalent Series Resistance). A ceramic capacitor with a low ESR value will provide the lowest voltage ripple and are therefore recommended. Due to its low ESR, the capacitance value can be calculated by the equation:

$$C_{out} = \frac{(V_O - V_{IN}) \times I_{OUT}}{V_{OUT} \times F_{SW} \times V_{ripple}}$$

In the equation above,  $V_{ripple}$  = peak to peak output ripple,  $F_{SW}$  is the switching frequency.

A 1μF~10μF ceramic capacitor is suitable for most application.

- Input Capacitor Selection

An input capacitor is required to supply the ripple current to the inductor, while limiting noise at the input source. A low ESR ceramic capacitors is required to keep the noise at the IC to a minimum.

A 4.7μF~10μF ceramic capacitor is suitable for most application. This capacitor must be connected very close to the VIN pin and inductor, with short traces for good noise performance.

- Schottky Diode Selection

The output rectifier diode conducts during the internal MOSFET is turn off. The average and peak current rating must be greater than the maximum output current and peak inductor current. The reverse breakdown voltage must be greater than the maximum output voltage. It is recommended to use a schottky diode with low forward voltage to minimize the power dissipation and therefore to maximize the efficiency of the converter. A 1N5819 type diode is recommended for HT7938 applications.

- LED Current Selection

The LED current is controlled by the current sense feedback resistor  $R_{fb}$ . The current sense feedback reference voltage is 200mV. In order to have accurate LED currents, precision resistors are the preferred type with a 1% tolerance. The LED current can be calculated from the following formula.

$$I_{LED} = \frac{V_{FB}}{R_{fb}} = \frac{200mV}{R_{fb}}$$

Where  $I_{LED}$  is the total output LED current,  $V_{FB}$ =feedback voltage,  $R_{fb}$ =current sense resistor.

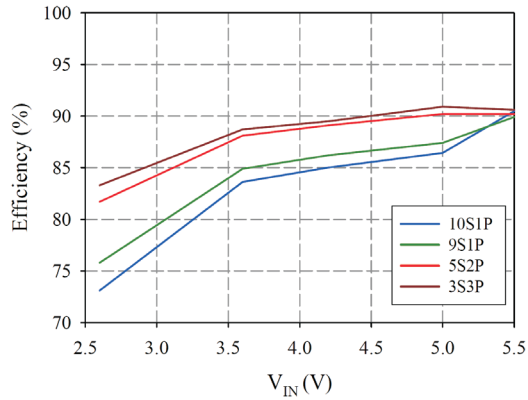
- Digital and Analog Dimming Control

The LED illumination level can be controlled using both digital and analog methods.

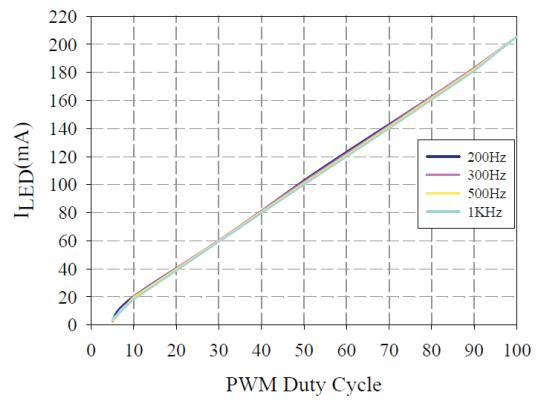
The digital method uses a PWM signal applied to the EN pin. This is shown in figure 7. The average LED current increases proportionally with the PWM signal duty cycle. A 0% duty cycle corresponds to zero LED current. A 100% duty cycle corresponds to full LED current. The PWM signal frequency should be set below 1kHz due to the delay time of device startup.

There are two methods of analog LED brightness control. The first method uses a DC voltage to control the feedback voltage. If the DC voltage range is from 0V to 3.3V, the selection of resistors control the LED current from 20mA to 0mA. The other way is to use a filtered PWM signal, as shown in figure 9. The filtered PWM signal application acts in the same way as the DC voltage dimming control.

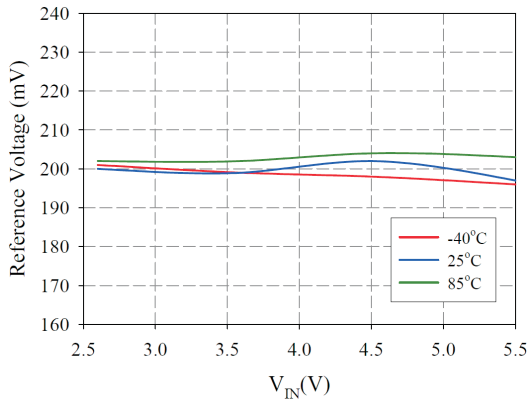
**Typical Performance Characteristics**



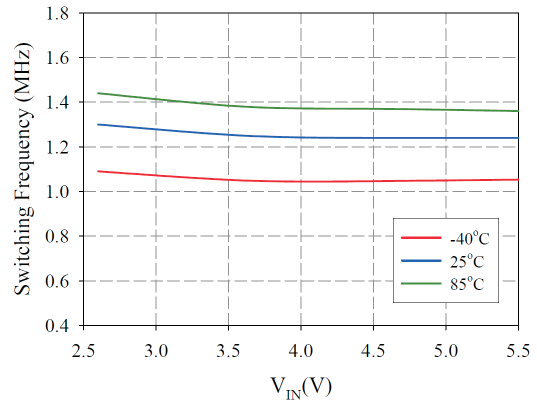
**Figure 1. Efficiency vs Input Voltage**



**Figure 2. LED Current vs PWM Dimming (9S1P LEDs)**

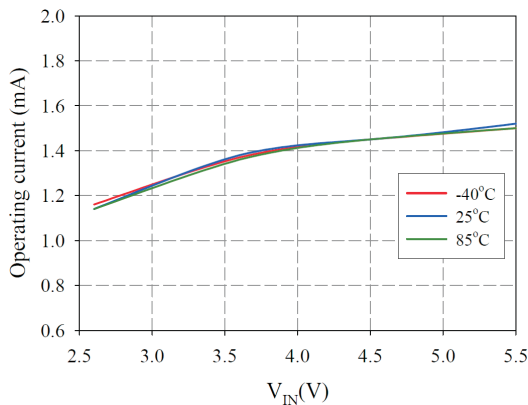


**Figure 3. Reference Voltage vs. Input Voltage**

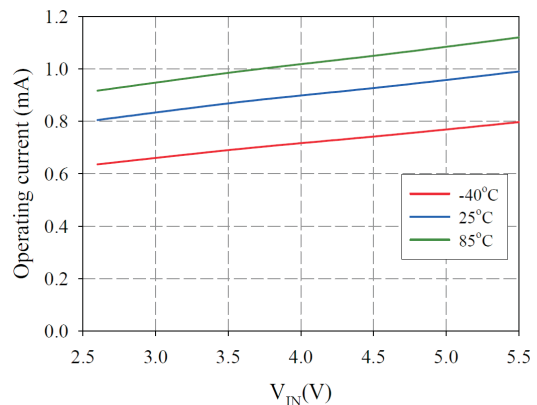


**Figure 4. Switching Frequency (MHz) vs. Input Voltage**

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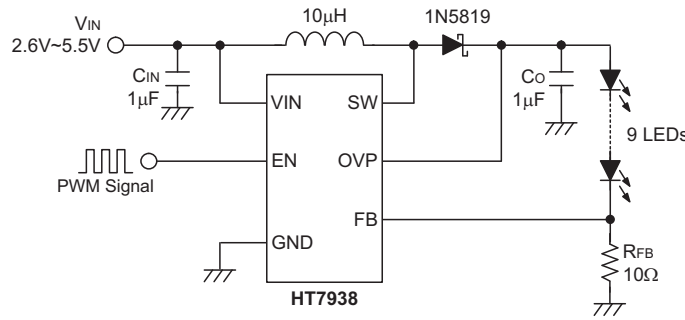


**Figure 5. Enable Voltage vs. Input Voltage**

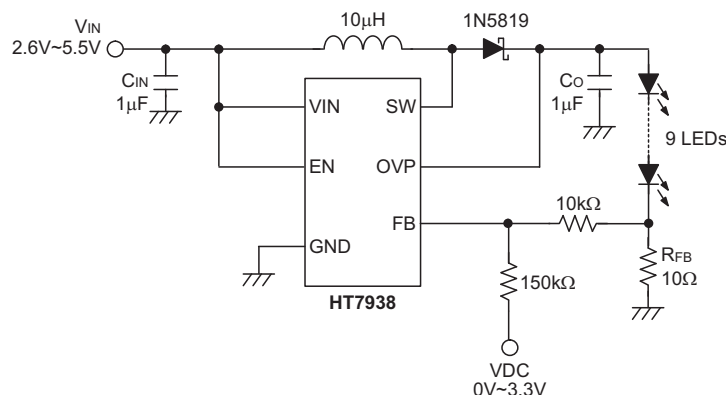


**Figure 6. Operating current vs. Input Voltage**

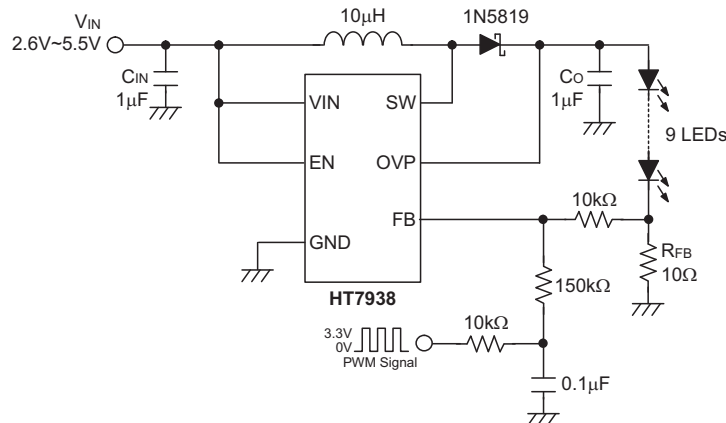
**Application Circuits**



**Figure 7. Application Circuits for Driving 9S1P WLEDs**



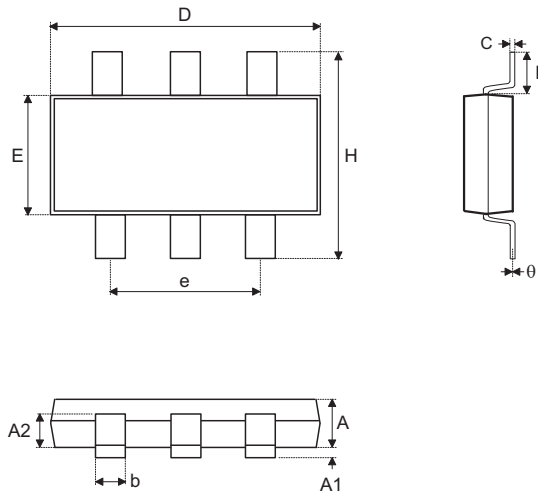
**Figure 8. Application Circuit for Dimming Control Using a DC Voltage**



**Figure 9. Application Circuit for Dimming Control Using a Filtered PWM Signal**

**Package Information**

**6-pin SOT23-6 Outline Dimensions**

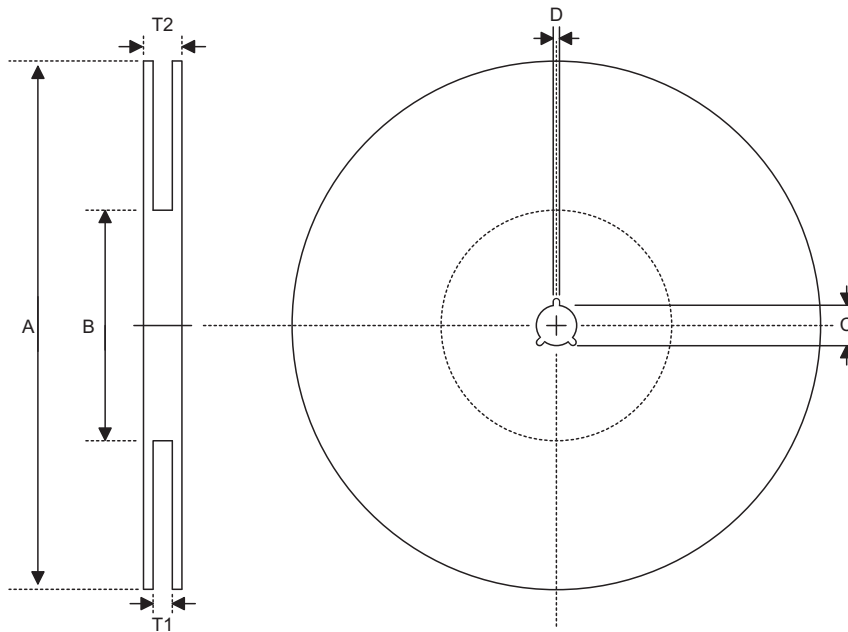


Symbol	Dimensions in mm		
	Min.	Nom.	Max.
A	1.0	—	1.3
A1	—	—	0.1
A2	0.7	—	0.9
b	0.35	—	0.50
C	0.10	—	0.25
D	2.7	—	3.1
E	1.4	—	1.8
e	—	1.9	—
H	2.6	—	3.0
L	0.37	—	—
$\theta$	1°	—	9°



**Product Tape and Reel Specifications**

**Reel Dimensions**

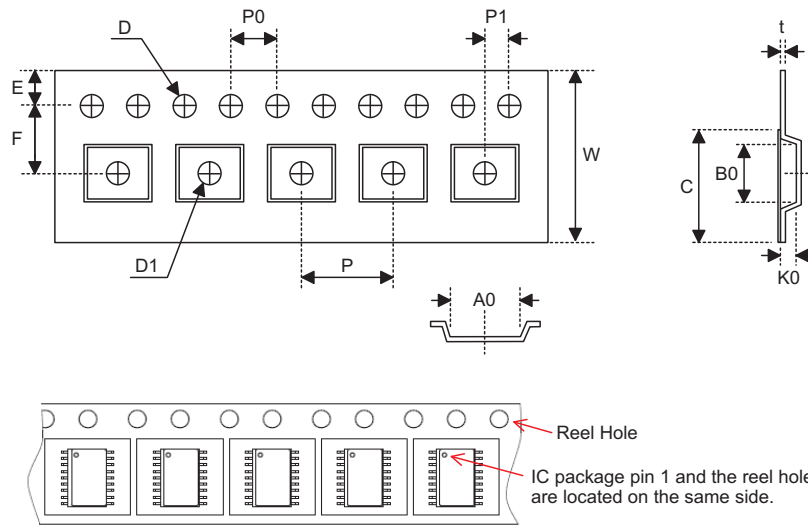


SOT23-6

Symbol	Description	Dimensions in mm
A	Reel Outer Diameter	178.0±1.0
B	Reel Inner Diameter	62.0±1.0
C	Spindle Hole Diameter	13.0±0.2
D	Key Slit Width	2.50±0.25
T1	Space Between Flange	8.4 <sup>+1.5/-0.0</sup>
T2	Reel Thickness	11.4 <sup>+1.5/-0.0</sup>

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**Carrier Tape Dimensions**



**SOT23-6**

Symbol	Description	Dimensions in mm
W	Carrier Tape Width	8.0±0.3
P	Cavity Pitch	4.0±0.1
E	Perforation Position	1.75±0.1
F	Cavity to Perforation (Width Direction)	3.50±0.05
D	Perforation Diameter	1.5 <sup>+0.1/-0.0</sup>
D1	Cavity Hole Diameter	1.5 <sup>+0.1/-0.0</sup>
P0	Perforation Pitch	4.0±0.1
P1	Cavity to Perforation (Length Direction)	2.00±0.05
A0	Cavity Length	3.15±0.10
B0	Cavity Width	3.2±0.1
K0	Cavity Depth	1.4±0.1
t	Carrier Tape Thickness	0.20±0.03
C	Cover Tape Width	5.3±0.1

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